

L Number	Hits	Search Text	DB	Time stamp
44	73	(((((shallow adj trench adj isolation) or STI)) and (photo\$1resist or resist)) and ((hydrogen or H?sub.2) same (anneal or annealing or thermal\$3 or treat\$3)) and (etch or etching)) and (polish or polishing or cmp or planarizie or (etch\$3 adj back))) and (epitaxial or epitaxy)	USPAT	2004/04/15 15:06
45	2602	trench same (epitaxial or epitaxy)	USPAT	2004/04/15 15:10
46	5185	trench same (epitaxial or epitaxy)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/15 15:07
47	839	(trench same (epitaxial or epitaxy)) and (hydrogen or H?sub.2)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/15 15:08
48	550	((trench same (epitaxial or epitaxy)) and (hydrogen or H?sub.2)) and (STI or isolation)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/15 15:08
49	326	((trench same (epitaxial or epitaxy)) and (hydrogen or H?sub.2)) and (STI or isolation)) and (cmp or polish or polishing or planarize or planarization)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/15 15:09
50	253	(((((trench same (epitaxial or epitaxy)) and (hydrogen or H?sub.2)) and (STI or isolation)) and (cmp or polish or polishing or planarize or planarization)) and (resist or photo\$1resist)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/15 15:09
52	3	Kwon-Jae-Soon.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/15 15:10
53	313	(trench same (epitaxial or epitaxy)) and ((hydrogen or H?sub.2) same trench)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/15 15:11
54	215	((trench same (epitaxial or epitaxy)) and ((hydrogen or H?sub.2) same trench)) and ((silicon adj nitride) or SiN or "Si.sub.3 N.sub.4")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/15 15:11
51	223	(((((trench same (epitaxial or epitaxy)) and (hydrogen or H?sub.2)) and (STI or isolation)) and (cmp or polish or polishing or planarize or planarization)) and (resist or photo\$1resist)) and (SiN or (silicon adj nitride) or "Si.sub.3 N.sub.4")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/15 15:11
-	5896	((shallow adj trench adj isolation) or STI)	USPAT	2003/09/25 14:02
-	3069	((shallow adj trench adj isolation) or STI)) and (photo\$1resist or resist)	USPAT	2003/09/25 14:03
-	799	((shallow adj trench adj isolation) or STI)) and (photo\$1resist or resist)) and (hydrogen or H?sub.2)	USPAT	2003/09/25 14:06
-	655	(((((shallow adj trench adj isolation) or STI)) and (photo\$1resist or resist)) and (hydrogen or H?sub.2)) and ((silicon adj nitride) or SiN or "Si.sub.3 N.sub.4")	USPAT	2003/09/25 14:05

-	304	(((((shallow adj trench adj isolation) or STI)) and (photo\$lresist or resist)) and ((hydrogen or H?sub.2) same (anneal or annealling or thermal\$3 or treat\$3)))	USPAT	2003/09/25 14:06
-	295	(((((shallow adj trench adj isolation) or STI)) and (photo\$lresist or resist)) and ((hydrogen or H?sub.2) same (anneal or annealling or thermal\$3 or treat\$3))) and (etch or etching)	USPAT	2003/09/25 14:07
-	221	((((((shallow adj trench adj isolation) or STI)) and (photo\$lresist or resist)) and ((hydrogen or H?sub.2) same (anneal or annealling or thermal\$3 or treat\$3))) and (etch or etching)) and (polish or polishing or cmp or planarizie or (etch\$3 adj back))	USPAT	2003/09/25 16:26
-	144	((((((shallow adj trench adj isolation) or STI)) and (photo\$lresist or resist)) and ((hydrogen or H?sub.2) same (anneal or annealling or thermal\$3 or treat\$3))) and (etch or etching)) and (polish or polishing or cmp or planarizie or (etch\$3 adj back)) and ((trench or isolation or sti).ab. or (trench or isolation or sti).clm.)	USPAT	2003/09/25 14:10
-	19	("4582565" "4666556" "4671970" "5087586" "5244827" "5246537" "5248625" "5385861" "5387538" "5455194" "5472903" "5854120" "5895253" "5915191" "5926717" "5989977" "6001705" "6022789" "6358785").PN.	USPAT	2003/09/25 14:13
-	26	("3990927" "4474975" "5156881" "5182221" "5410176" "5470798" "5719085" "5741740" "5776557" "5786039" "5801083" "5863827" "5883006" "5888880" "5895253" "5904540" "5930645" "5943585" "5950094" "5960299" "5972773" "5998280" "6030881" "6051447" "6156674" "6300219").PN.	USPAT	2003/09/25 14:18
-	62	((((((shallow adj trench adj isolation) or STI)) and (photo\$lresist or resist)) and ((hydrogen or H?sub.2) same (anneal or annealling or thermal\$3 or treat\$3))) and (etch or etching)) and (polish or polishing or cmp or planarizie or (etch\$3 adj back))) and (epitaxial or epitaxy)	USPAT	2004/04/15 15:06
-	62	((((((shallow adj trench adj isolation) or STI)) and (photo\$lresist or resist)) and ((hydrogen or H?sub.2) same (anneal or annealling or thermal\$3 or treat\$3))) and (etch or etching)) and (polish or polishing or cmp or planarizie or (etch\$3 adj back))) and (epitaxial or epitaxy)	USPAT	2003/09/26 09:25